NSN 5961-00-493-6115

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-493-6115 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-48 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1.2 forward voltage, average and 2.2 forward voltage, peak and 2.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 150.00 amperes source cutoff current absolute and 8.00 milliamperes source cutoff current outside diameter and 8.00 milliamperes forward current, average nanoamperes and 35.00 milliamperes forward current, total rms preset and 50.00 milliamperes forward current, total rms peak **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 18338-113977 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure:**

Fiig:

No

Demilitarization: